

Computer simulation and analysis of the use of new doping profiles in junctionless field effect transistor to reduce the off-current and the threshold voltage

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In this study, we first simulate the JLTFET in the Silvaco environment. Due to the importance of extinguishing current and threshold voltage in this transistor, we discontinue the field effect using new damping patterns of extinction current and threshold voltage. Device engineering has a direct impact on the leakage current of the transducer field effect. Using computer simulation, we try to deliver the best results in reducing shutdown current and threshold voltage. In this study, we simulate and analyze the effect of doping and material engineering techniques on JLTFET extinction current and threshold voltage.

Keywords : Non-junction field effect transistor, blackout current, threshold voltage

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